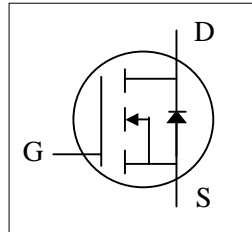




- ▼ Simple Drive Requirement
- ▼ Lower Gate Charge
- ▼ Fast Switching Characteristics
- ▼ RoHS Compliant & Halogen-Free

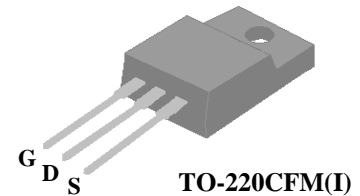


$BV_{DSS}$	100V
$R_{DS(ON)}$	16.5m $\Omega$
$I_D$	31.7A

### Description

AP55T10 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-220CFM package is widely preferred for all commercial-industrial through hole applications. The mold compound provides a high isolation voltage capability and low thermal resistance between the tab and the external heat-sink.



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	+20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	31.7	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	20	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	120	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	36.7	W
$P_D@T_A=25^\circ C$	Total Power Dissipation	1.92	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	3.4	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	65	$^\circ C/W$



# AP55T10GI-HF

## Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=24A$	-	-	16.5	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	5	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=24A$	-	44	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V$	-	-	25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}= \pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge	$I_D=24A$	-	70	112	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=80V$	-	16	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	34	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=50V$	-	19	-	ns
$t_r$	Rise Time	$I_D=10A$	-	27	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\ \Omega$	-	37	-	ns
$t_f$	Fall Time	$V_{GS}=10V$	-	17	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	3400	5440	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	320	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	200	-	pF
$R_g$	Gate Resistance	$f=1.0\text{MHz}$	-	1	2	$\Omega$

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=24A, V_{GS}=0V$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_S=10A, V_{GS}=0V$	-	70	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	250	-	nC

### Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

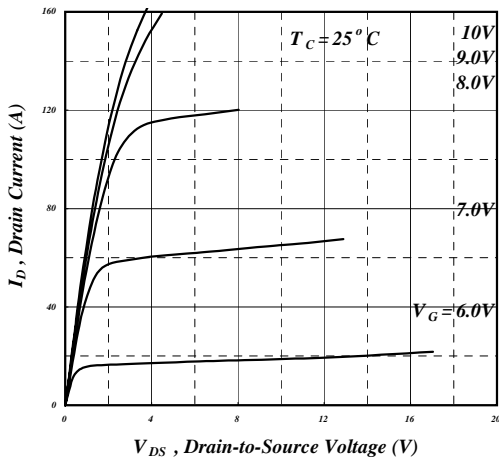


Fig 1. Typical Output Characteristics

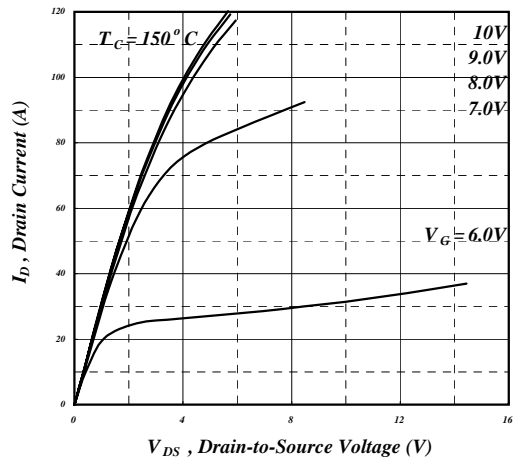


Fig 2. Typical Output Characteristics

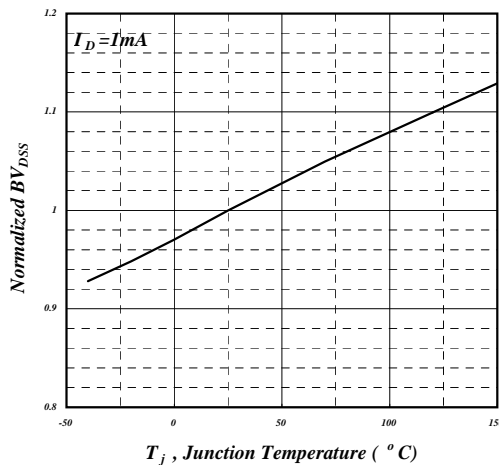


Fig 3. Normalized  $BV_{DSS}$  v.s. Junction Temperature

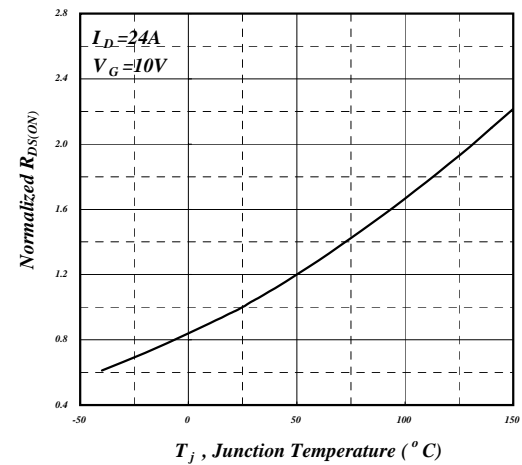


Fig 4. Normalized On-Resistance v.s. Junction Temperature

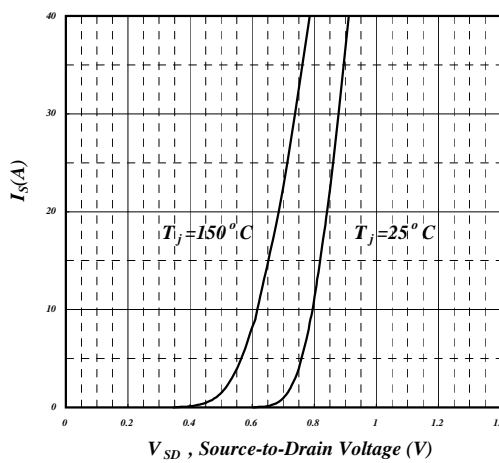


Fig 5. Forward Characteristic of Reverse Diode

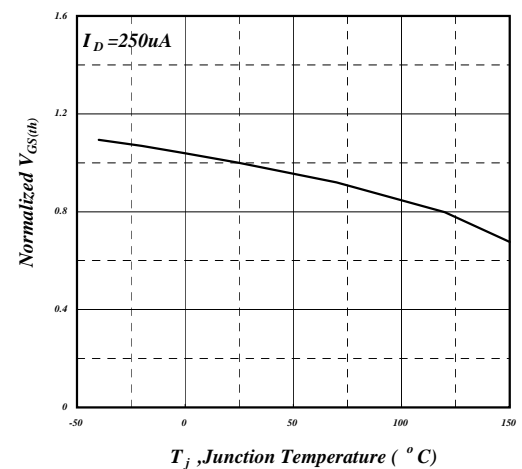


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



# AP55T10GI-HF

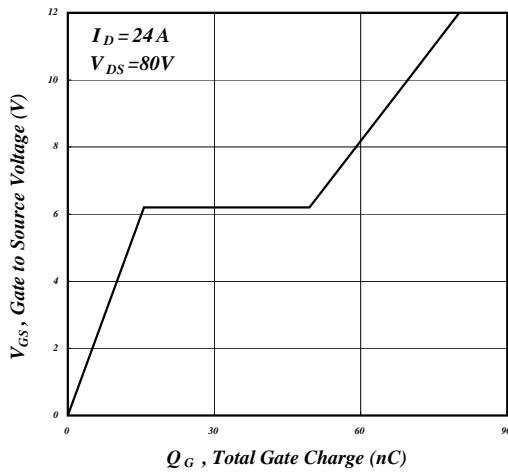


Fig 7. Gate Charge Characteristics

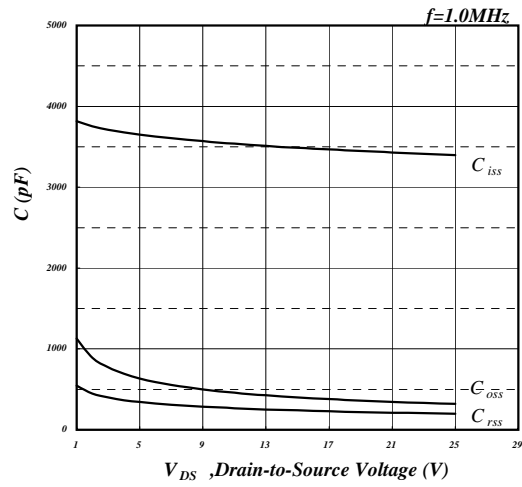


Fig 8. Typical Capacitance Characteristics

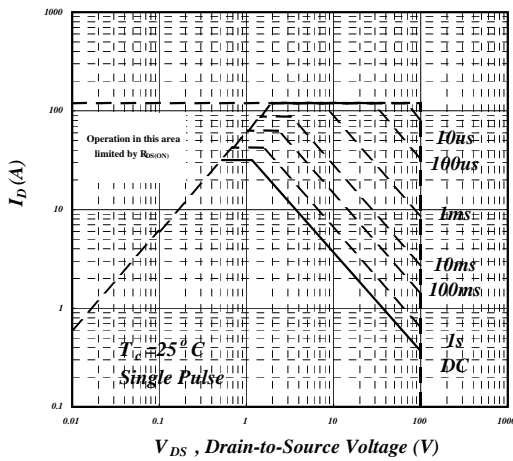


Fig 9. Maximum Safe Operating Area

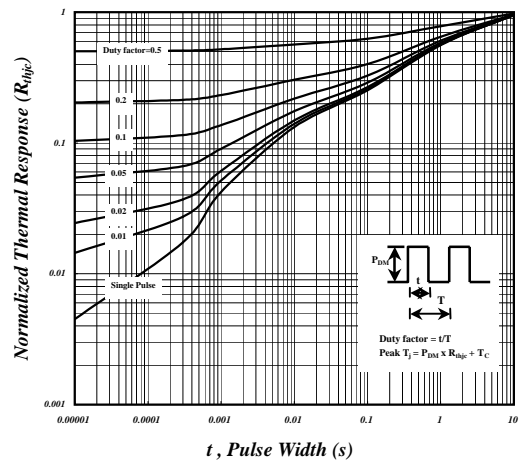


Fig 10. Effective Transient Thermal Impedance

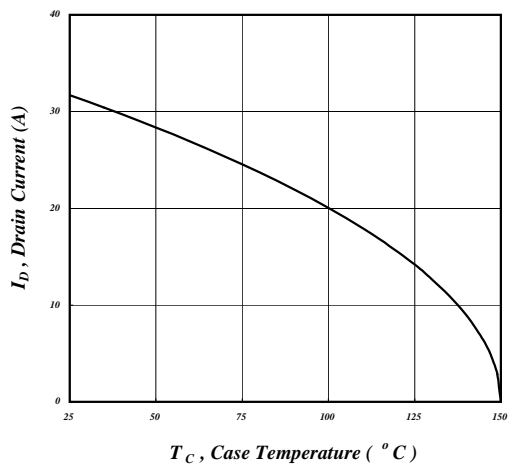


Fig 11. Maximum Continuous Drain Current v.s. Case Temperature

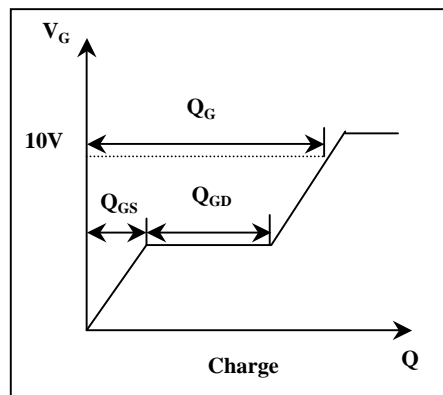


Fig 12. Gate Charge Waveform